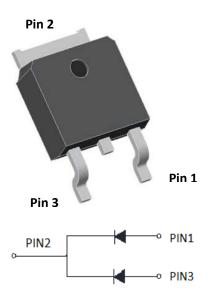


MBR1060CD





Schottky Diodes

Features

- High frequency operation
- High purity, high temperature epoxy encapsulation for enhanced mechanical strength and moisture resistance
- Guard ring for enhanced ruggedness and long term reliability

Typical Applications

Typical applications are in switching power supplies, converters, freewheeling diodes, and reverse battery protection.

Mechanical Data

• Package: TO-252

Molding compound meets UL 94 V-0 flammability

rating, RoHS-compliant

• Terminals: Tin plated leads, solderable per J-STD-

002 and JESD22-B102

• Polarity: As marked

■Maximum Ratings (Ta=25°C Unless otherwise specified)

PARAMETER	SYMBOL	UNIT	MBR1060CD
Device marking code			MBR1060CD
Repetitive Peak Reverse Voltage	VRRM	V	60
Average Rectified Output Current @60Hz sine wave, R-load, $T_a {=} 25^{\circ}\!$	Ю	Α	10
Surge(Non-repetitive)Forward Current @ $60H_Z$ half sine-wave, 1 cycle, T_a =25 $^{\circ}$ C	IFSM	Α	120
Current Squared Time @1ms≤t<8.3ms Tj=25℃,	I ² t	A ² s	60
Storage Temperature	T _{stg}	$^{\circ}$	-55 ~ +1 50
Junction Temperature	Tj	${\mathbb C}$	-55 ~ +150

■Electrical Characteristics (Ta=25°C Unless otherwise specified)

PARAMETER	SYMBOL	UNIT	TEST CONDITIONS	MBR1060CD
Maximum instantaneous forward voltage drop per diode	VFM	٧	IFM=5.0A	0.72
Maximum DC reverse current at rated DC blocking voltage per diode	IRRM1		VRM=VRRM T _a =25°C	0.2
	IRRM2	mA	VRM=VRRM T _a =125°C	50

MBR1060CD

Thermal Characteristics $(T_a=25^{\circ}\mathbb{C} \text{ Unless otherwise specified})$

PARAMETER		SYMBOL UNIT		MBR1060CD	
Thermal Resistance	Between junction and case	R _{θJ-C}	°C M	5.0	

■Ordering Information (Example)

PREFERED P/N	UNIT WEIGHT(g)	MINIIMUM PACKAGE(pcs)	INNER BOX QUANTITY(pcs)	OUTER CARTON QUANTITY(pcs)	DELIVERY MODE
MBR1060CD	Approximate 0.32	2500	2500	25000	Reel

140

120

100

80

60

40

20

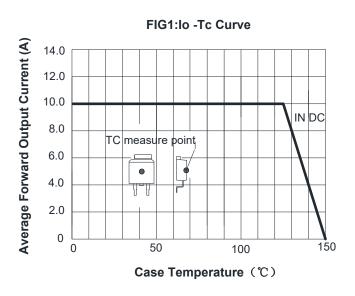
1

2

5

Peak Forward Surge Current (A)

■Characteristics (Typical)



8.3ms Single
Half Sine-Wave
JEDEC Method

10

Number of Cycles

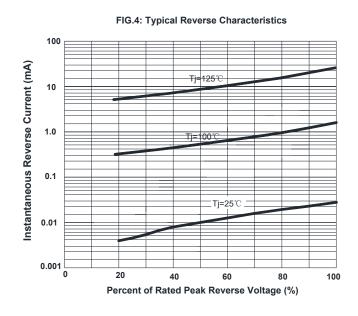
50

100

FIG2:Surge Forward Current Capability

FIG3: Forward Voltage

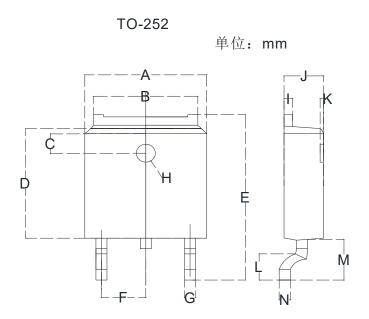
100
60
20
10
5.0
1.0
0.5
0.2
0.1
0.1
0.2
0.3
0.4
0.5
0.6
0.7
0.8
0.9
1.0
1.1
1.2
Instantaneous Forward Voltage (V)







■Outline Dimensions



TO-252					
Dim	Min	Max			
Α	6.500	6.700			
В	5.100	5.460			
С	1.400	1.800			
D	6.000	6.200			
Е	10.000	10.400			
F	2.166	2.366			
G	0.660	0.860			
Н	Ф1.050	Ф1.350			
I	0.460	0.580			
J	2.200	2.400			
K	0	0.300			
L	0.890	2.290			
M	2.730	3.080			
N	0.430	0.580			



MBR1060CD

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